

1.Scope

The present specifications shall apply to an SJPZ-N33.

2.Outline

Type	Silicon Diode
Structure	Resin Molded
Applications	Over Voltage Absorption

3.Flammability

UL94V-0 (Equivalent)

4. Absolute maximum ratings

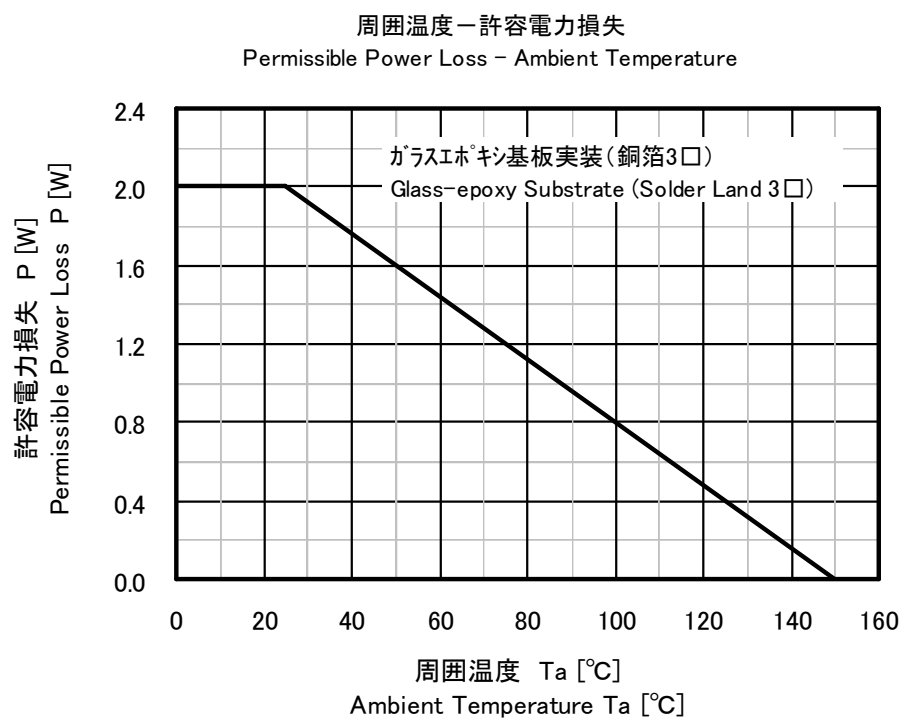
No.	Item	Symbol	Unit	Rating	Conditions
1	Permissible Power loss	P	W	2	Refer to Derating of 6
2	Transient Peak Reverse Power	P _{RSM}	W	500	Single Square Wave
3	Junction Temperature	T _j	°C	-55~+150	—
4	Storage Temperature	T _{stg}	°C	-55~+150	—

5. Electrical characteristics(Ta=25°C , unless otherwise specified)

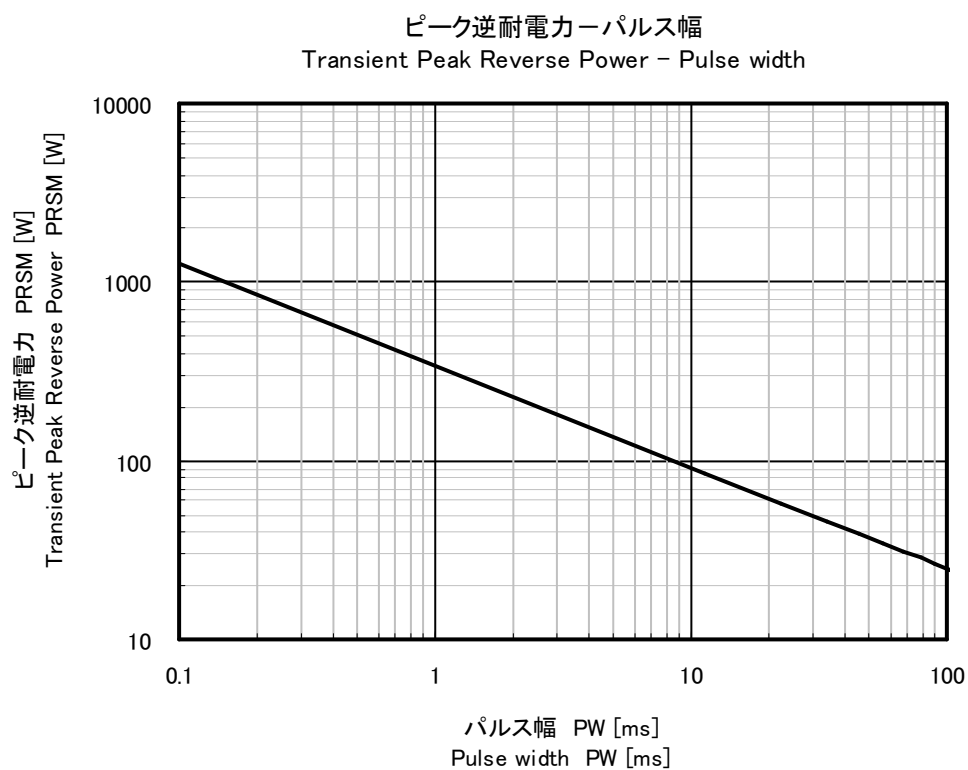
No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V _F	V	1.2 max.	I _F =2A
2	Reverse Breakdown Voltage	V _Z	V	31.0~35.0	I _Z =1mA
3	Reverse Leakage Current	I _R	uA	1 max.	V _R =25V
4	Temperature Coefficient Breakdown Voltage	γ _z	mV/°C	29 typ.	I _Z =1mA
5	Equivalent Resistance of Breakdown Region	R _z	Ω	5 typ.	I _z =10mA~20mA

6. Derating

Permissible Power Loss

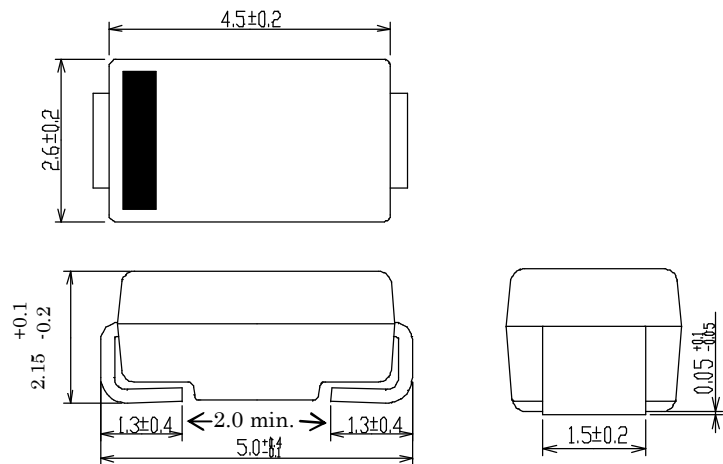


7. Transient Peak Reverse Power Rating



8. Package information

8-1 Package type, physical dimensions

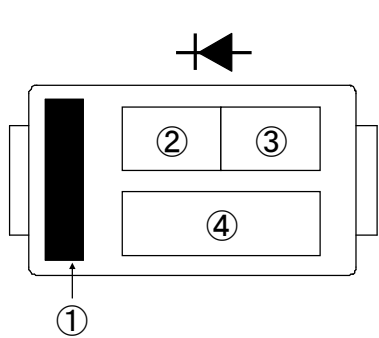


Dimensions in mm

8-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3 Marking



- 1 Polarity marking (Cathode band)
- 2 Type number
SJPZ-N as abbreviated of ZN.
- 3 Vz Class number
33V as abbreviated of 33.
- 4 Lot number
Example) 9615
9: Last number of Year
6: Month from 1 to 9 for Jan. to Sep. O for Oct., N for Nov., D for Dec.
15: Day.

